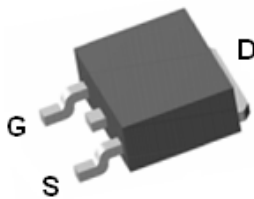


# TD304BH

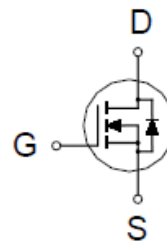
## N-Channel Enhancement Mode MOSFET

### PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
30V	9m $\Omega$ @ $V_{GS} = 10V$	57A



TO-252



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	57	A
	$T_C = 100\text{ }^{\circ}\text{C}$		37	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	150	
Avalanche Current		$I_{AS}$	29	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	40	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	$P_D$	54	W
	$T_C = 100\text{ }^{\circ}\text{C}$		21	
Junction & Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^{\circ}\text{C}$

### THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.3	$^{\circ}\text{C} / \text{W}$

<sup>1</sup> Pulse width limited by maximum junction temperature.

# TD304BH

## N-Channel Enhancement Mode MOSFET

### ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^{\circ}\text{C}$ , Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.6	2.8	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24V, V_{GS} = 0V$			1	$\mu A$
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			10	
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 20A$		11.5	18	m $\Omega$
		$V_{GS} = 10V, I_D = 20A$		7.5	9	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 5V, I_D = 20A$		35		S
DYNAMIC						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		900		pF
Output Capacitance	$C_{oss}$			185		
Reverse Transfer Capacitance	$C_{rss}$			120		
Gate Resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.4		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V$ $I_D = 20A$		22		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			5		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			6.5		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DS} = 15V,$ $I_D \cong 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		15		nS
Rise Time <sup>2</sup>	$t_r$			25		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			60		
Fall Time <sup>2</sup>	$t_f$			18		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ( $T_J = 25\text{ }^{\circ}C$ )						
Continuous Current	$I_S$				57	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 20A, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	$t_{rr}$	$I_F = 20A, di_F/dt = 100A / \mu S$		23		nS
Reverse Recovery Charge	$Q_{rr}$			15		nC

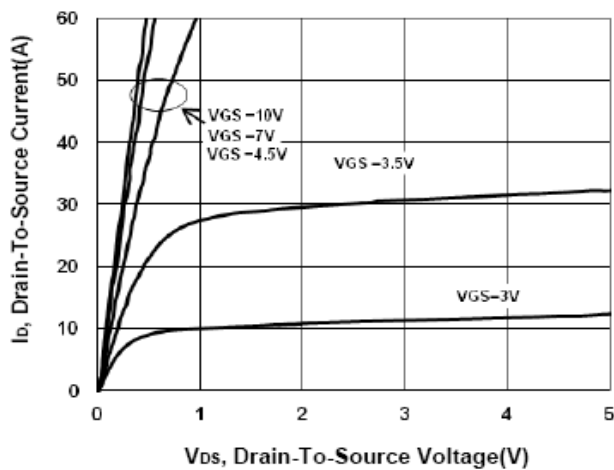
<sup>1</sup> Pulse test : Pulse Width  $\leq 300\text{ }\mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup> Independent of operating temperature.

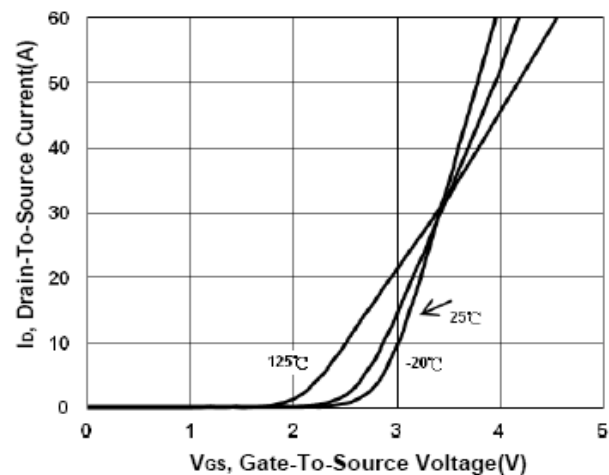
## TD304BH

### N-Channel Enhancement Mode MOSFET

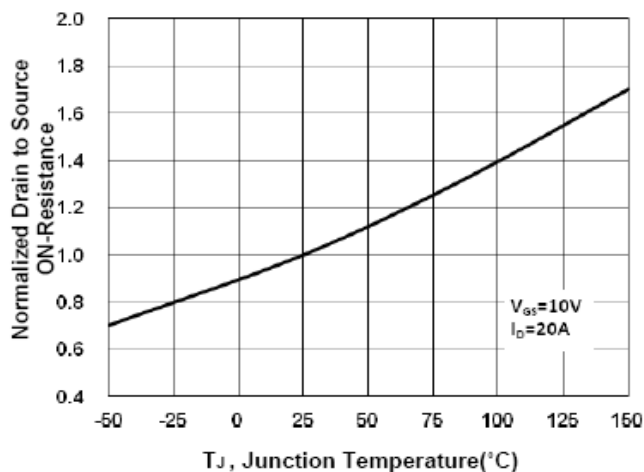
**Output Characteristics**



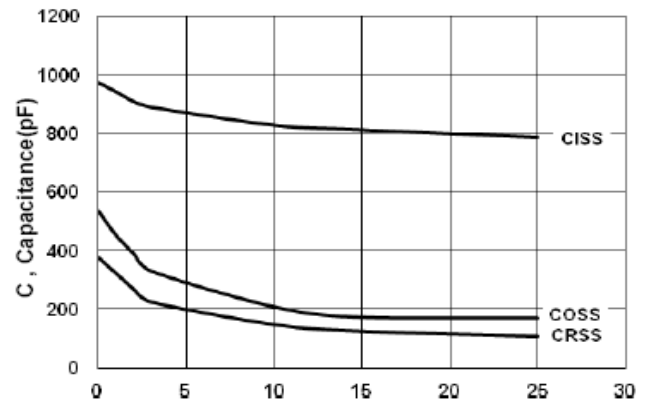
**Transfer Characteristics**



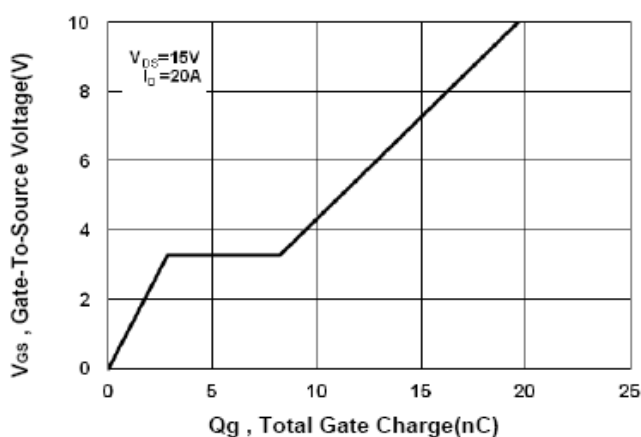
**On-Resistance VS Temperature**



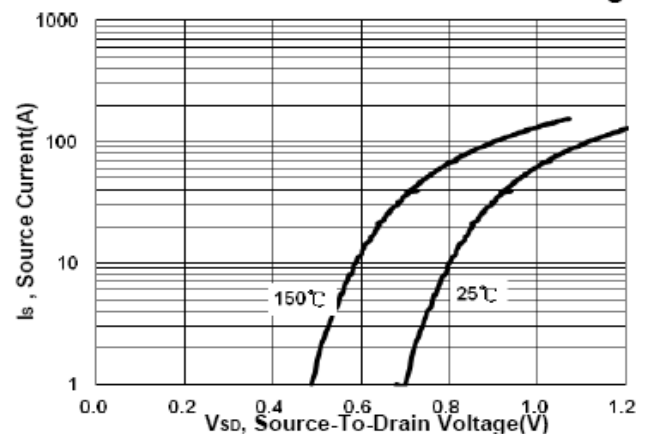
**Capacitance Characteristic**



**Gate charge Characteristics**



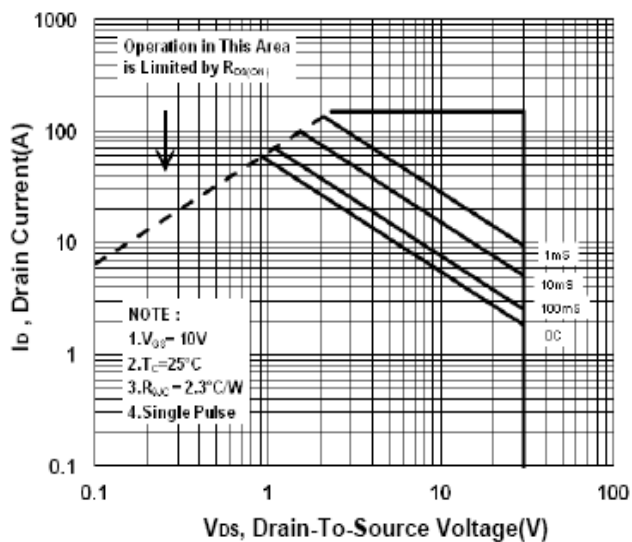
**Source-Drain Diode Forward Voltage**



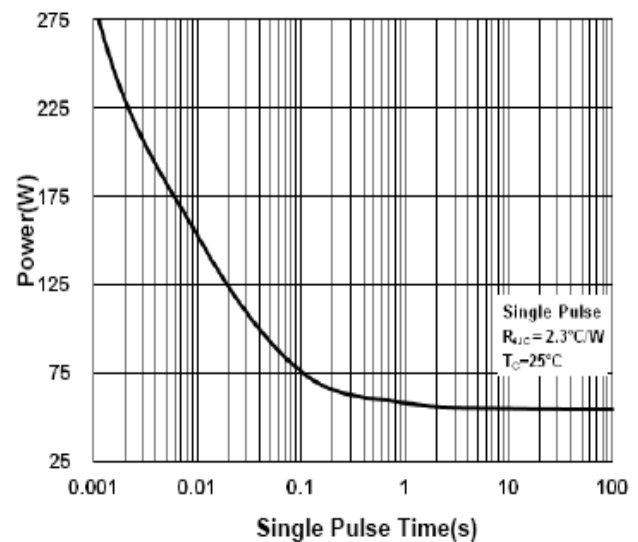
# TD304BH

## N-Channel Enhancement Mode MOSFET

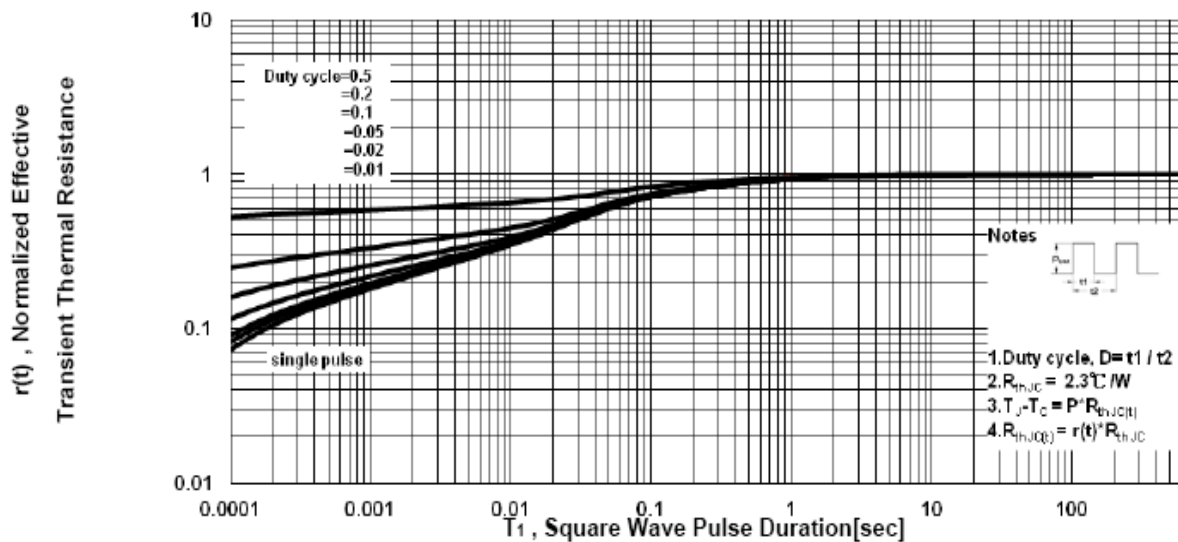
**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**



# TD304BH

## N-Channel Enhancement Mode MOSFET

### Package Dimension

### TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.4	K	0.15		1.1
C	0.4	0.5	0.61	L	0.4	0.76	0.89
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.4	0.5	0.61	S	4.9	5.1	5.3
F	0		0.2	T	4.6	4.75	5.44
G	5.3	6.1	6.3	U	1.4		1.78
H	0.9		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8				

